

Silicon PNP Power Transistors

2SA636 2SA636A

DESCRIPTION

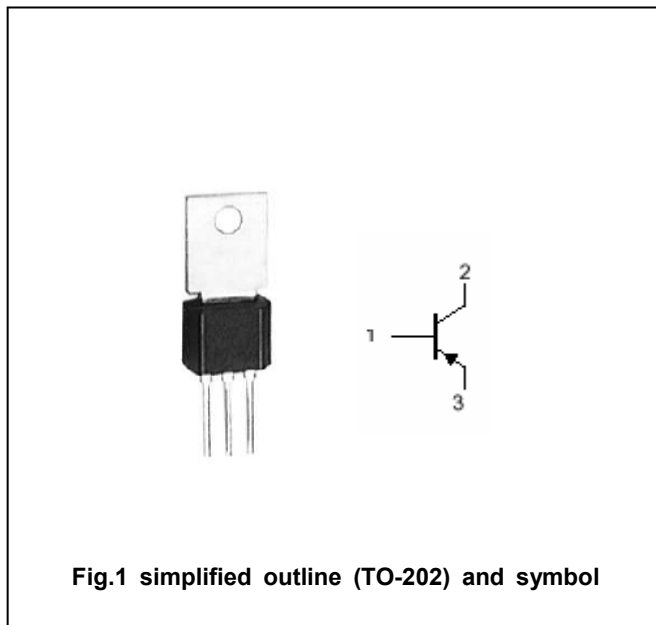
- With TO-202 package
- Complement to type 2SC1098/1098A
- High breakdown voltage
- High transition frequency

APPLICATIONS

- For audio frequency power amplifier and low speed switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-70	V
V _{CEO}	Collector-emitter voltage	2SA636	-45	V
		2SA636A	-60	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-3	A
I _{CM}	Collector current-peak		-5	A
I _B	Base current		-0.6	A
P _T	Total power dissipation	T _C =25°C	10	W
		T _a =25°C	1.2	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A ; I _B =-0.15A		-0.5	-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.5A ; I _B =-0.15A		-0.8	-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-45V; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-20mA ; V _{CE} =-5V	20			
h _{FE-2}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	40		250	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		60		pF
f _T	Transition frequency	I _C =-0.1A ; V _{CB} =-5V		45		MHz

◆ h_{FE-2} classifications

N	M	L	K
40-60	50-100	80-160	120-250

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PACKAGE OUTLINE

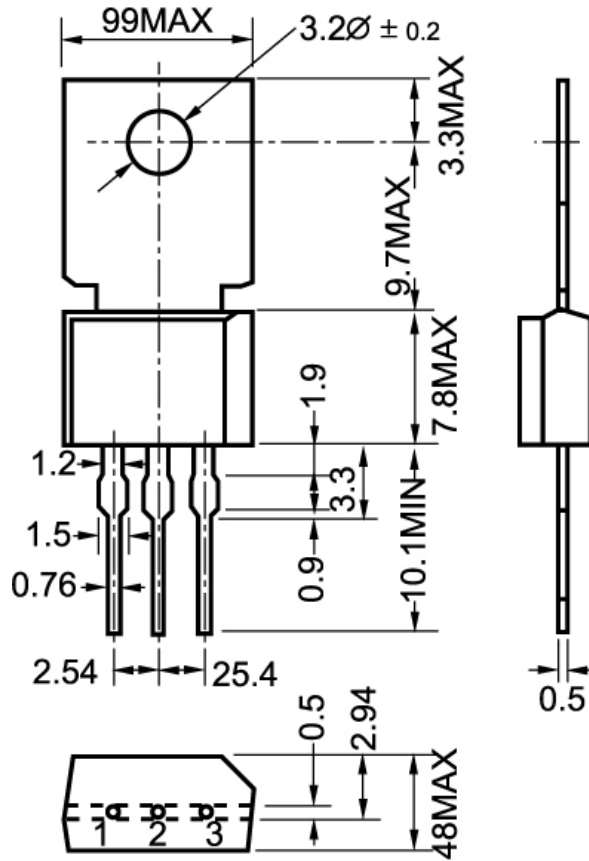


Fig.2 outline dimensions